

**WHAT IS CLAIMED IS:**

1. A semiconductor device comprising:
  - a channel region provided over a substrate and between a source region and a drain region;
  - a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;
  - a first insulating film comprising silicon nitride provided over said channel region and said source region and said drain region and said gate electrode and said gate insulating film;
  - a second insulating film provided over said first insulating film and comprising resin to provide a first leveled surface over said first insulating film;
  - a drain electrode connected with said drain region and provided over said second insulating film;
  - a source electrode connected with said source region and provided over said second insulating film
  - a third insulating film provided over said drain electrode and said source electrode and comprising resin to provide a second leveled surface over said drain electrode and said source electrode;
  - a black matrix provided over said third insulating film;
  - a fourth insulating film provided over said black matrix and comprising resin to provide a third leveled surface over said black matrix; and
  - a pixel electrode connected with one of said drain electrode and said source electrode and provided over said fourth insulating film.
2. A device according to claim 1 wherein said channel region and said source region and said drain region are provided in a semiconductor film comprising a plurality of radial crystal grains of silicon.
3. A device according to claim 2 wherein said semiconductor film has a thickness of 100 to 750 Å.
4. A device according to claim 1 wherein said semiconductor device is

incorporated into one selected from the group consisting of a portable intelligent terminal, a head mounted display, a car navigational system, a mobile telephone, a portable video camera, and a projection display.

5. A device according to claim 1 wherein said semiconductor device is incorporated into a liquid crystal display.

6. A device according to claim 1 wherein said semiconductor device is incorporated into an electroluminescent display.

7. A semiconductor device comprising:

- a channel region provided over a substrate and between a source region and a drain region;

- a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;

- a first insulating film comprising silicon nitride provided over said channel region and said source region and said drain region and said gate electrode and said gate insulating film;

- a second insulating film provided over said first insulating film and comprising polyimide to provide a first leveled surface over said first insulating film;

- a drain electrode connected with said drain region and provided over said second insulating film;

- a source electrode connected with said source region and provided over said second insulating film

- a third insulating film provided over said drain electrode and said source electrode and comprising polyimide to provide a second leveled surface over said drain electrode and said source electrode;

- a black matrix provided over said third insulating film;

- a fourth insulating film provided over said black matrix and comprising polyimide to provide a third leveled surface over said black matrix; and

- a pixel electrode connected with one of said drain electrode and said source electrode and provided over said fourth insulating film.

8. A device according to claim 7 wherein said channel region and said source region and said drain region are provided in a semiconductor film comprising a plurality of radial crystal grains of silicon.
9. A device according to claim 8 wherein said semiconductor film has a thickness of 100 to 750 Å.
10. A device according to claim 7 wherein said semiconductor device is incorporated into one selected from the group consisting of a portable intelligent terminal, a head mounted display, a car navigational system, a mobile telephone, a portable video camera, and a projection display.
11. A device according to claim 7 wherein said semiconductor device is incorporated into a liquid crystal display.
12. A device according to claim 7 wherein said semiconductor device is incorporated into an electroluminescent display.
13. A semiconductor device comprising:  
a channel region provided over a substrate and between a source region and a drain region;  
a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;  
a first insulating film comprising silicon nitride provided over said channel region and said source region and said drain region and said gate electrode and said gate insulating film;  
a second insulating film provided over said first insulating film and comprising resin to provide a first leveled surface over said first insulating film;  
a drain electrode connected with said drain region and provided over said second insulating film;  
a source electrode connected with said source region and provided over said second insulating film

a third insulating film provided over said drain electrode and said source electrode and comprising resin to provide a second leveled surface over said drain electrode and said source electrode;

a black matrix provided over said third insulating film;

a fourth insulating film provided over said black matrix and comprising resin to provide a third leveled surface over said black matrix; and

a pixel electrode connected with one of said drain electrode and said source electrode and provided over said fourth insulating film,

wherein at least a part of said black matrix is in contact with at least a part of said one of said drain electrode and said source electrode.

14. A device according to claim 13 wherein said channel region and said source region and said drain region are provided in a semiconductor film comprising a plurality of radial crystal grains of silicon.

15. A device according to claim 14 wherein said semiconductor film has a thickness of 100 to 750 Å.

16. A device according to claim 13 wherein said semiconductor device is incorporated into one selected from the group consisting of a portable intelligent terminal, a head mounted display, a car navigational system, a mobile telephone, a portable video camera, and a projection display.

17. A device according to claim 13 wherein said semiconductor device is incorporated into a liquid crystal display.

18. A device according to claim 13 wherein said semiconductor device is incorporated into an electroluminescent display.